

TOSHIBA INTEGRATED IGBT MODULE SILICON N CHANNEL IGBT

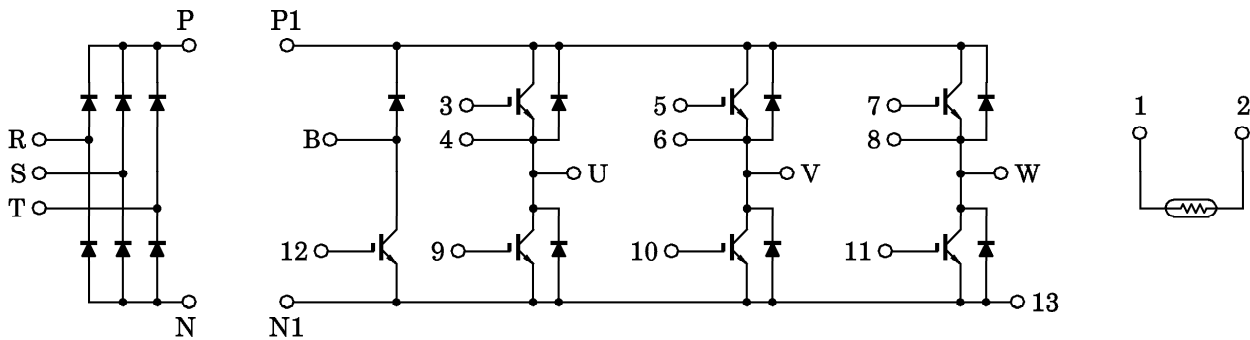
# MIG30J906H, MIG30J906HA

HIGH POWER SWITCHING APPLICATIONS

MOTOR CONTROL APPLICATIONS

- Integrates Inverter, Converter and Brake Power Circuits and Thermistor in One Package.
- Output (Inverter Stage) : 3φ 30A/600V IGBT
- Input (Converter Stage) : 3φ 30A/800V Silicon Rectifier
- The Electrodes are Isolated from Case.
- Outline
  - MIG30J906H : 2-108E3A
  - MIG30J906HA : 2-108E4A
- Weight : 190g

EQUIVALENT CIRCUIT



961001EAA2

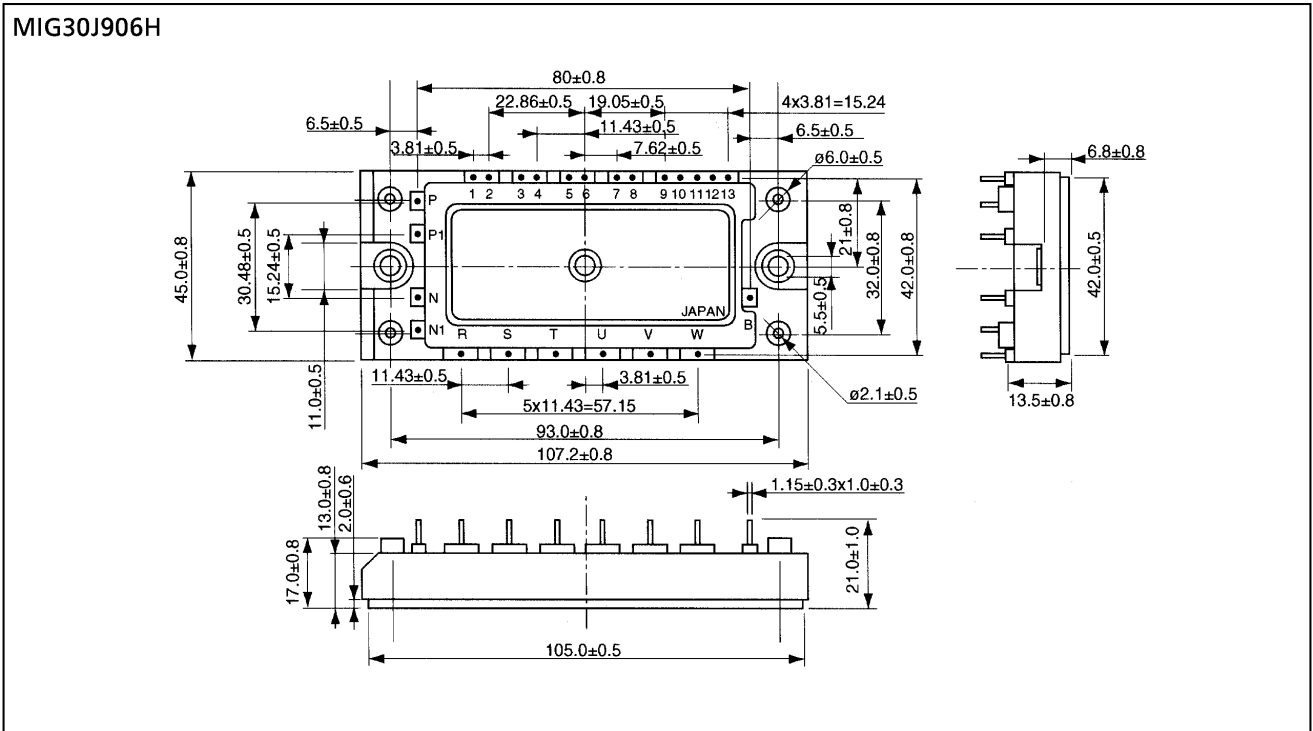
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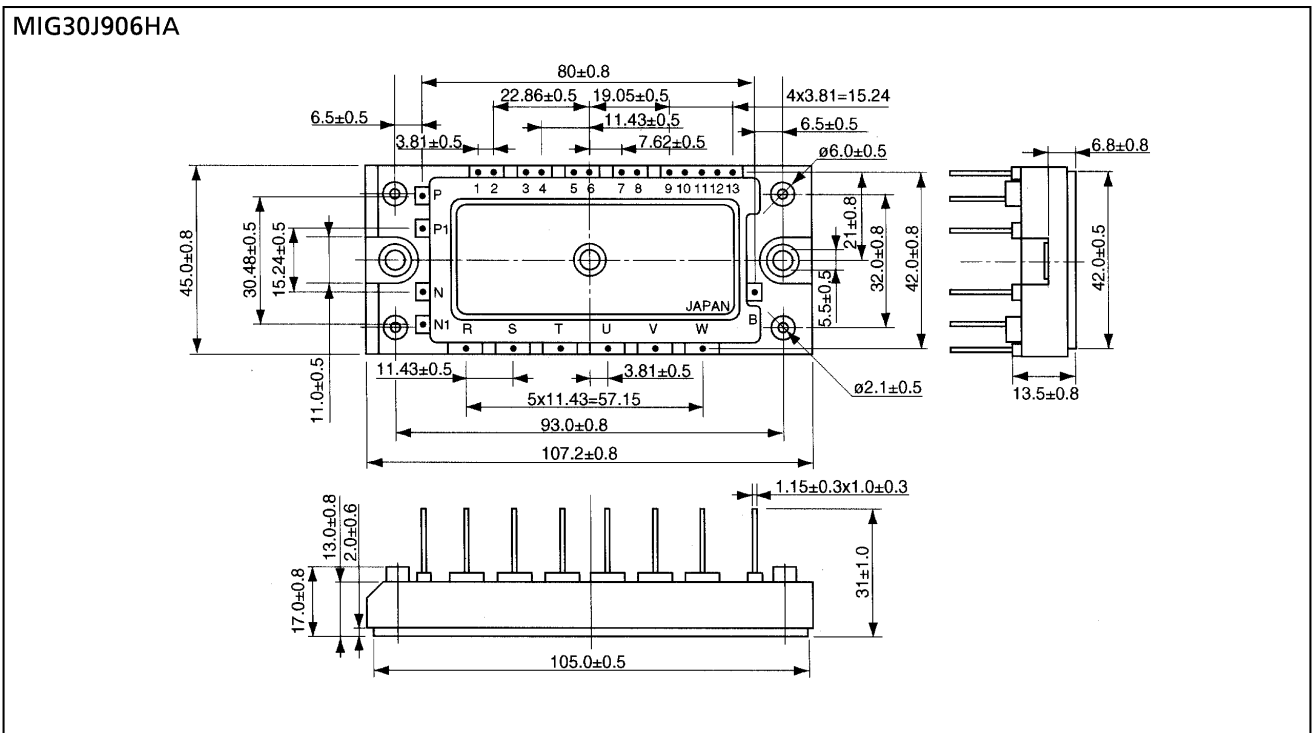
**Package Dimension**

Unit : mm



2-108E3A

Unit : mm



2-108E4A

MAXIMUM RATINGS (Ta = 25°C)

STAGE		CHARACTERISTIC		SYMBOL	RATING	UNIT
Inverter	Collector-Emitter Voltage			V <sub>CES</sub>	600	V
	Gate-Emitter Voltage			V <sub>GES</sub>	±20	V
	Collector Current	DC		I <sub>C</sub>	35 / 30	A
		1ms		I <sub>CP</sub>	70 / 60	A
	Forward Current	DC		I <sub>F</sub>	30	A
		1ms		I <sub>FM</sub>	60	A
Collector Power Dissipation (T <sub>c</sub> = 25°C)			P <sub>C</sub>	125	W	
Converter	Repetitive Peak Reverse Voltage			V <sub>R</sub> RM	800	V
	Average Output Rectified Current			I <sub>O</sub>	30	A
	Peak One Cycle Surge Forward Current (50Hz, Non-Repetitive)			I <sub>F</sub> SM	400	A
Brake	IGBT	Collector-Emitter Voltage		V <sub>CES</sub>	600	V
		Gate-Emitter Voltage		V <sub>GES</sub>	±20	V
		Collector Current	DC	I <sub>C</sub>	35 / 30	A
			1ms	I <sub>CP</sub>	70 / 60	A
	Collector Power Dissipation (T <sub>c</sub> = 25°C)			P <sub>C</sub>	125	W
	FWD	Reverse Voltage		V <sub>R</sub>	600	V
		Forward Current	DC	I <sub>F</sub>	30	A
			1ms	I <sub>FM</sub>	60	A
Module	Junction Temperature		T <sub>j</sub>	150	°C	
	Storage Temperature Range		T <sub>stg</sub>	-40~125	°C	
	Isolation Voltage		V <sub>Isol</sub>	2500 (AC 1 minute)	V	
	Screw Torque		—	6	N·m	

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

a. Inverter stage

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		$I_{GES}$	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	±500	nA
Collector Cut-Off Current		$I_{CES}$	$V_{CE} = 600V, V_{GE} = 0$	—	—	1.0	mA
Gate-Emitter Cut-Off Voltage		$V_{GE} (off)$	$I_C = 3mA, V_{CE} = 5V$	5.0	—	8.0	V
Collector-Emitter Saturation Voltage		$V_{CE} (sat)$	$I_C = 30A$	—	2.1	2.7	V
			$V_{GE} = 15V$				
Input Capacitance		$C_{ies}$	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	—	—	pF
Switching Time	Rise Time	$t_r$	$V_{CC} = 300V$ $I_C = 30A$ $V_{GE} = \pm 15V$ $R_G = 43\Omega$  (Note 1)	—	0.10	0.20	$\mu s$
	Turn-On Time	$t_{on}$		—	0.25	0.50	
	Fall Time	$t_f$		—	0.15	0.30	
	Turn-Off Time	$t_{off}$		—	0.50	0.80	
Forward Voltage		$V_F$	$I_F = 30A, V_{GE} = 0$	—	2.0	2.8	V
Reverse Recovery Time		$t_{rr}$	$I_F = 30A, V_{GE} = -10V$ $di / dt = 100A / \mu s$	—	0.08	0.15	$\mu s$
Thermal Resistance		$R_{th(j-c)}$	Transistor	—	—	1.0	°C / W
			Diode	—	—	2.6	

b. Converter stage

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Repetitive Peak Reverse Current		$I_{RRM}$	$V_{RRM} = 800V$	—	—	50	$\mu A$
Peak Forward Voltage		$V_{FM}$	$I_{FM} = 30A$	—	1.05	1.20	V
Peak One Cycle Surge Forward Current		$I_{FSM}$	50Hz sine-half-wave	400	—	—	A
Thermal Resistance		$R_{th(j-c)}$	—	—	—	1.56	°C / W

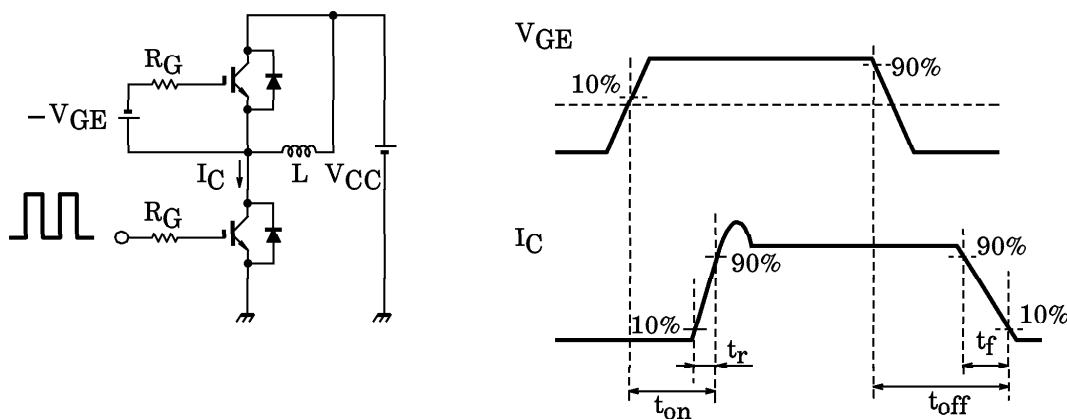
c. Brake stage

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		$I_{GES}$	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	$\pm 500$	nA
Collector Cut-Off Current		$I_{CES}$	$V_{CE} = 600V, V_{GE} = 0$	—	—	1.0	mA
Reverse Current		$I_R$	$V_R = 600V$	—	—	1.0	mA
Gate-Emitter Cut-Off Voltage		$V_{GE} (off)$	$I_C = 3mA, V_{CE} = 5V$	5.0	—	8.0	V
Collector-Emitter Saturation Voltage		$V_{CE} (sat)$	$I_C = 30A$	—	2.1	2.7	V
			$V_{GE} = 15V$	—	2.2	2.8	
Input Capacitance		$C_{ies}$	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	—	—	pF
Switching Time	Rise Time	$t_r$	$V_{CC} = 300V$ $I_C = 30A$ $V_{GE} = \pm 15V$ $R_G = 43\Omega$  (Note 1)	—	0.10	0.20	$\mu s$
	Turn-On Time	$t_{on}$		—	0.25	0.50	
	Fall Time	$t_f$		—	0.15	0.30	
	Turn-Off Time	$t_{off}$		—	0.50	0.80	
Forward Voltage		$V_F$	$I_F = 30A, V_{GE} = 0$	—	2.0	2.8	V
Thermal Resistance		$R_{th(j-c)}$	Transistor	—	—	1.0	$^{\circ}C/W$
			Diode	—	—	2.6	

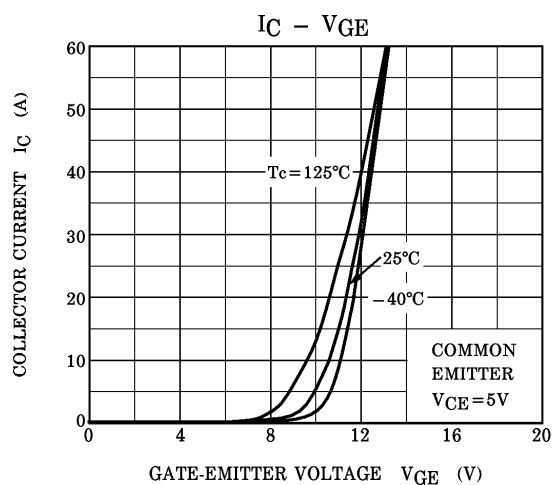
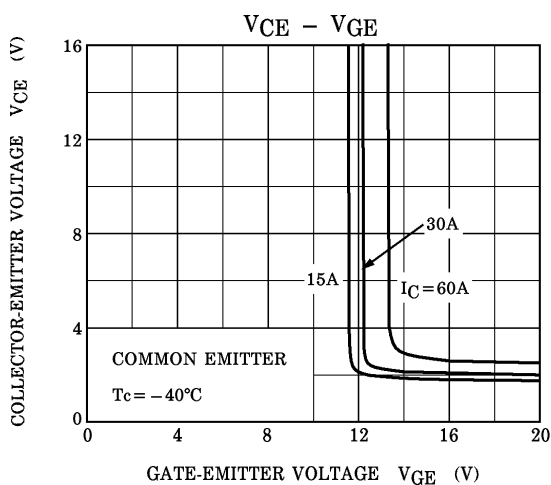
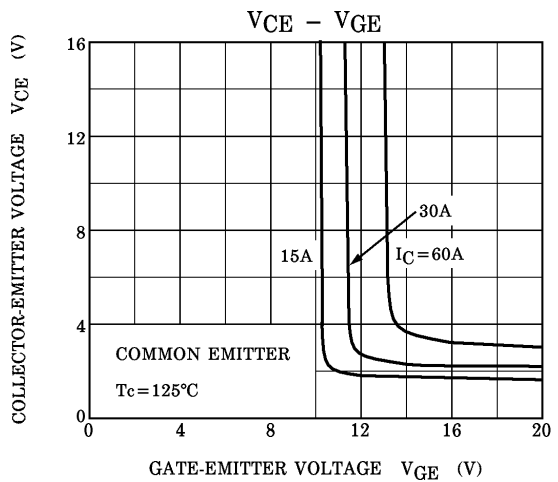
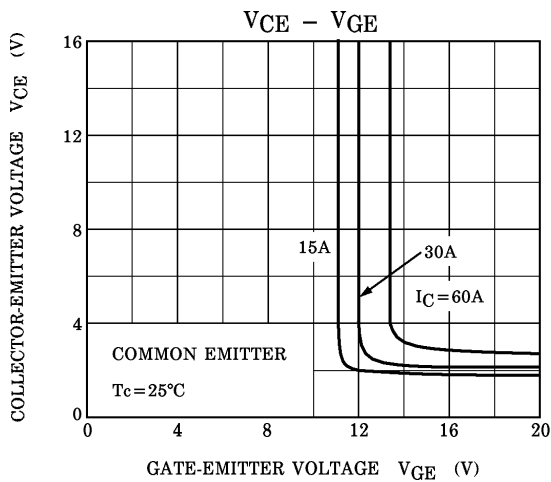
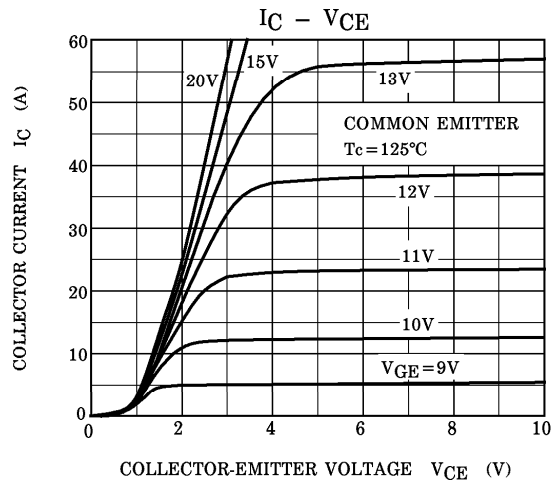
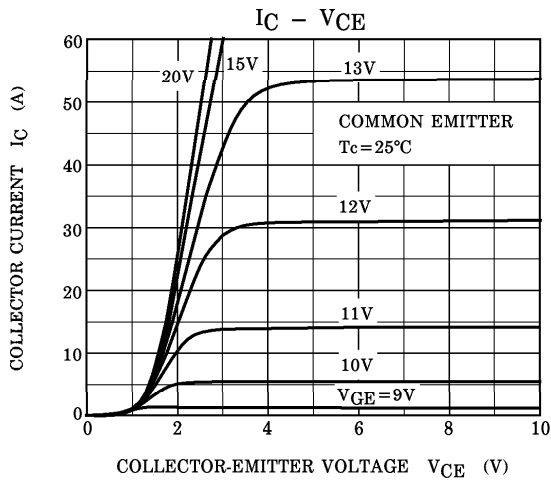
d. Thermistor

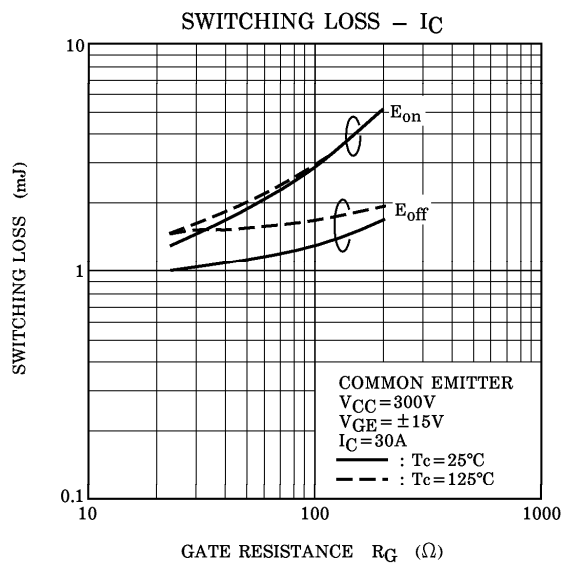
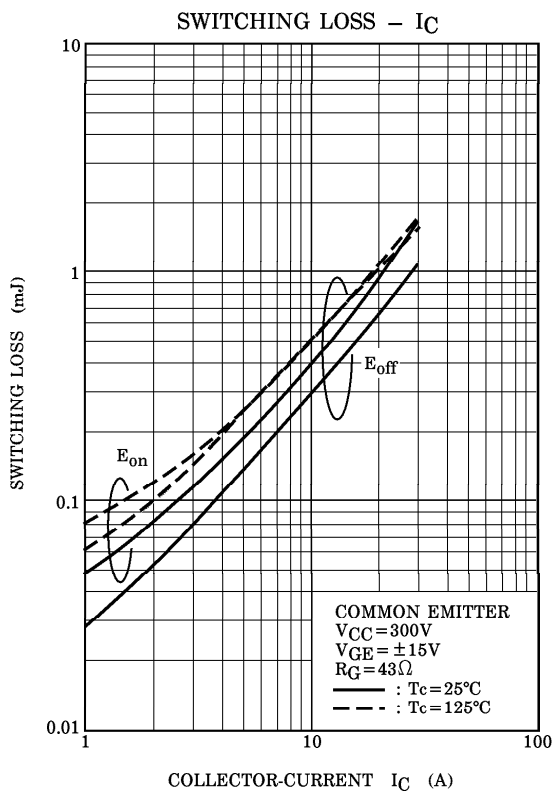
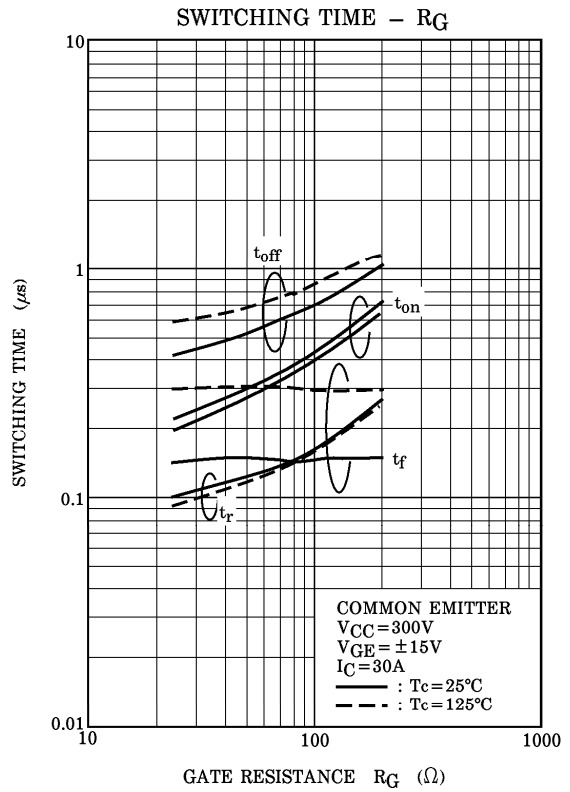
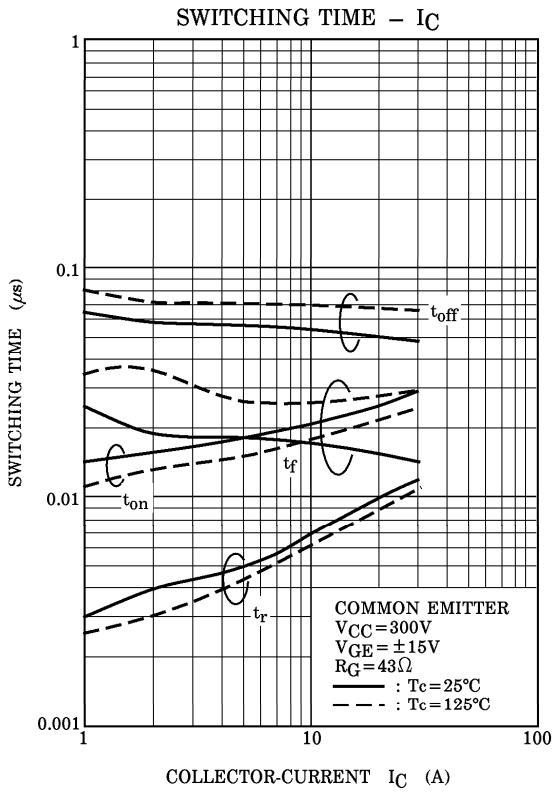
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Zero-power Resistance	$R_{25}$	$I_{TM} = 0.2mA, T_c = 25^{\circ}C$	17.31	20	23.14	k $\Omega$
B Value	$B_{25/85}$	$T_c = 25^{\circ}C / T_c = 85^{\circ}C$	—	3760	—	K

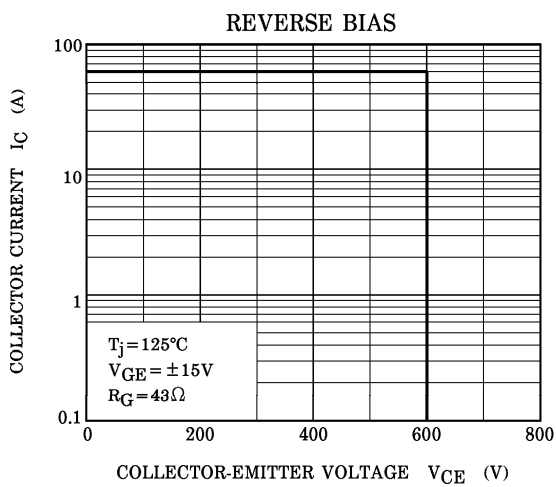
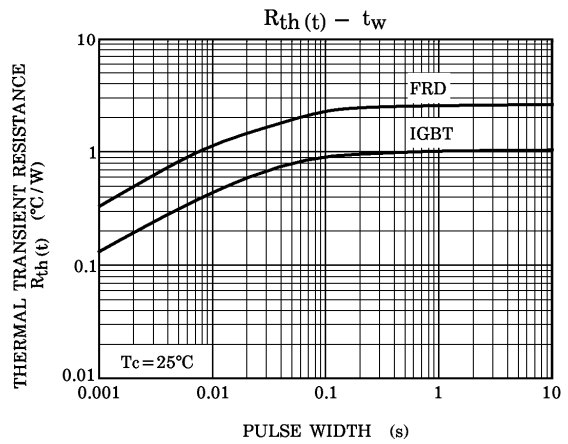
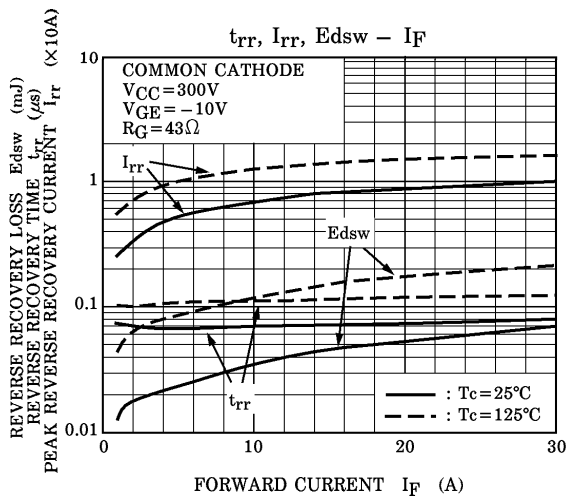
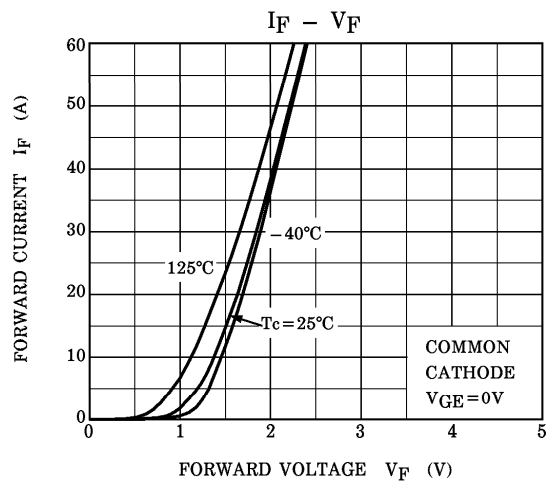
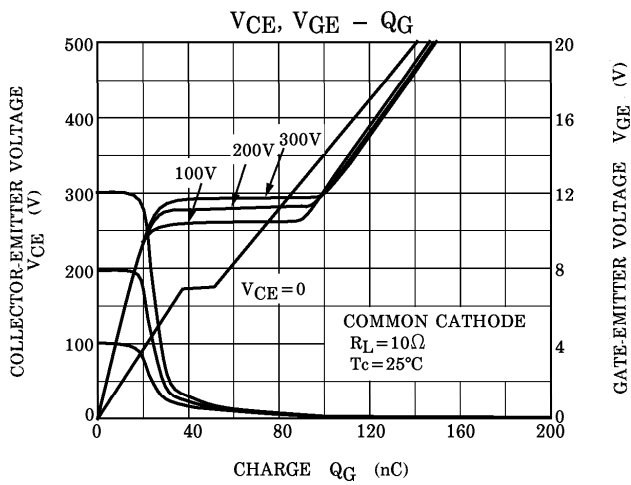
(Note 1) Switching Time Test Circuit & Timing Chart



a. Inverter stage / c. Brake stage









b. Converter stage

